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IN THE CLAIMS

1 (Previously Presented). A method comprising:

forming a phase change memory element having a holding voltage that is at least 80 percent of the threshold voltage of the element and a holding voltage greater than about .9 volts.

Claim 2 (Canceled).

- 3 (Original). The method of claim 1 including forming a phase change memory element to have a threshold voltage that does not vary by more than 10 percent with programming currents varying as much as two times.
- 4 (Original). The method of claim 1 including forming a phase change memory element including a phase change material between a pair of electrodes.
- 5 (Original). The method of claim 4 including forming a phase change material with a lower electrode of titanium silicon nitride.
 - 6 (Previously Presented). An apparatus comprising:
- a phase change memory element to be read with a voltage greater than or equal to the threshold voltage of the element, said element having a holding voltage that is at least 80 percent of the threshold voltage of the element.
- 7 (Original). The apparatus of claim 6 wherein said element includes an upper and a lower electrode and a phase change material between said electrodes.

Claim 8 (Canceled).

9 (Original). The apparatus of claim 6 wherein the phase change memory element has a threshold voltage that varies by less than 10 percent with varying programming currents.

10 (Original). The apparatus of claim 7 wherein said lower electrode includes titanium silicon nitride or carbon.

11 (Previously Presented). A system comprising:

a processor; and

a phase change memory element having a holding voltage that is at least 80 percent of the threshold voltage of the element and said holding voltage being at least about .9 volts.

- 12 (Previously Presented). The system of claim 11 wherein said wireless interface includes a dipole antenna.
- 13 (Original). The system of claim 11 wherein said element includes an upper and lower electrode and a phase change material between said electrodes.
- 14 (Original). The system of claim 13 wherein said lower electrode includes titanium silicon nitride.

Claim 15 (Canceled).

16 (Original). The system of claim 11 wherein the phase change memory element has a threshold voltage that does not vary by more than 10 percent with programming currents varying by as much as two times.

Claims 17-19 (Canceled).